


## PATENT

PTO-1449  Information Disclosure Citation in an Application			Application No. <b>Unassigned</b>		Applicant(s): <b>STARIKOV ET AL.</b>		
			Docket Number <b>065238.0128</b>		Group Art Unit <b>2814</b>		Filing Date <b>08/18/2003</b>
<b>U.S. PATENT DOCUMENTS</b>							
		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
WSL	A	6,075,611	06/13/2000	DUSSAN V. ET AL.	356	432	05/07/1998
	B	6,034,404	03/07/2000	SOARES	257	415	12/05/1996
	C	5,955,972	09/21/1999	WADE	340	960	09/03/1997
	D	5,995,229	11/30/1999	OMI	356	374	09/22/1998
	E	5,990,500	11/23/1999	OKAZAKI	257	99	03/03/1999
	F	5,920,018	07/06/1999	WILKERSON, ET AL.	73	861.41	12/11/1996
	G	5,822,473	10/13/1998	MAGEL, ET AL.	385	12	02/28/1997
	H	5,591,963	01/07/1997	TAKEDA, ET AL.	250	214.1	08/08/1995
	I	5,442,169	08/15/1995	KUNZ	250	227.21	06/02/1993
	J	5,341,805	08/30/1994	STAVRIDIS ET AL.	128	633	04/06/1993
	K	5,202,571	04/13/1993	HIRABAYSHI, ET AL.	257	10	07/03/1991
	L	5,196,709	03/23/1993	BERNDT, ET AL.	250	458.1	05/03/1991
	M	5,082,629	01/21/1992	BURGESS, JR., ET AL.	422	82.11	12/29/1989
✓	N	4,900,373	02/13/1990	CHU, ET AL.	148	33.4	07/19/1989
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES      NO
<b>NON-PATENT DOCUMENTS</b>							
		DOCUMENT (Including Author, Title, Source, and Pertinent Pages)					DATE
WSL	O	TEMPEZ, ET AL., "PHOTOENHANCED REACTIVE ION ETCHING OF III-V NITRIDES IN BCL <sub>3</sub> /CL <sub>2</sub> /AR/N <sub>2</sub> PLASMAS," <i>J. VAC. SCI. TECHNOL. A</i> 17(4), JUL/AUG 1999, PG. 2209-2213					1999
	P	MEDELICI, ET AL., "REACTIVE ION ETCHING OF BORON NITRIDE AND GALLIUM NITRIDE MATERIALS IN CL <sub>2</sub> /AR AND BCL <sub>3</sub> /CL <sub>2</sub> /AR CHEMISTRIES," <i>MAT. RES. SOC. SYMP. PROC. VOL. 512</i> , PG. 285-291					1998
	Q	STARIKOV, ET AL., "A HOT ELECTRONS-BASED WIDE SPECTRUM ON-ORBIT OPTICAL CALIBRATION SOURCE," <i>SPACE TECHNOLOGY AND APPLICATIONS INTERNATIONAL FORUM-1998</i> , PG. 648-653					1998
✓	R	STARIKOV, ET AL., "METAL-INSULATOR-SEMICONDUCTOR SCHOTTKY BARRIER STRUCTURES FABRICATED USING INTERFACIAL BN LAYERS GROWN ON GAN AND SIC FOR OPTOELECTRONIC DEVICE APPLICATIONS," <i>J. VAC. SCI. TECHNOL. A</i> 17(4), JUL/AUG 1999, PG. 1235-1238					1999
EXAMINER					DATE CONSIDERED		
					<b>12/8/04</b>		
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.							